Silicon NPN Power Transistors 2SC1161

DESCRIPTION

·With TO-66 package
·Low collector saturation voltage

APPLICATIONS

·For low frequency high voltage power amplifier TV vertical deflection output applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	120	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		1	A
P_D	Total power dissipation	T_C=25?	15	W
T_j	Junction temperature		150	?
T_{stg}	Storage temperature		-55~150	?

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CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA ;I_B=0	120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=500mA; I_B=50mA			1.5	V
$V_{BE\ sat}$	Base-emitter saturation voltage	I_C=500mA; I_B=50mA			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=120V; I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0			1.0	μA
h_{FE}	DC current gain	I_C=200mA ; V_{CE}=5V	30		200	
f_T	Transition frequency	I_C=200mA ; V_{CE}=10V	5			MHz

PACKAGE OUTLINE

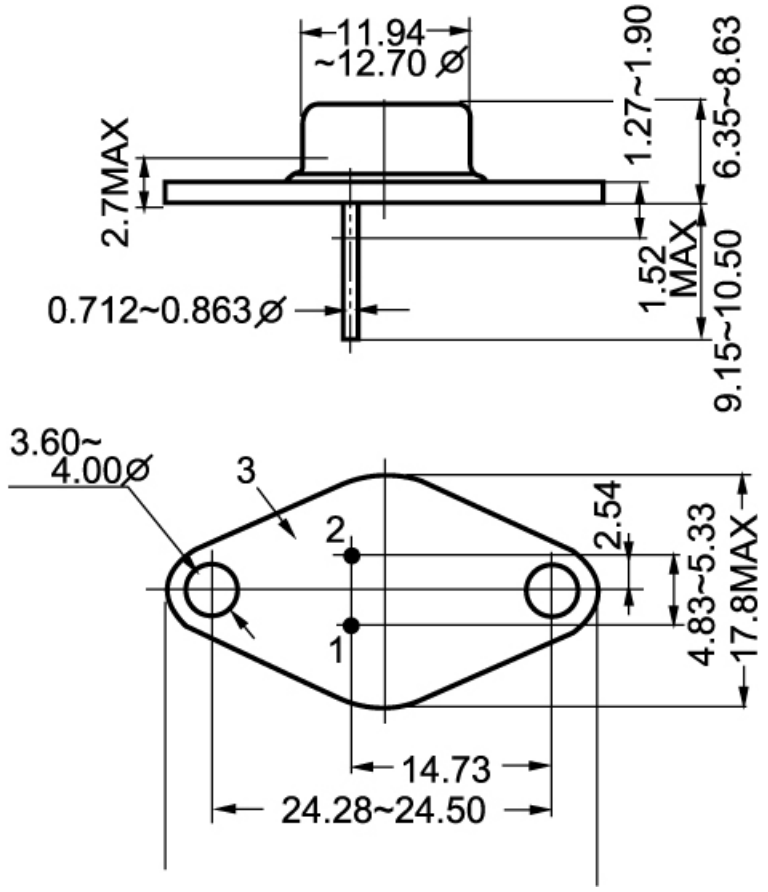

Fig.2 outline dimensions